

ABSTRACT

A method and system for providing a semiconductor device is described. The semiconductor includes a core and a periphery. The method and system include providing a plurality of core gate stacks in the core, a plurality of sources in the core and a plurality of periphery gate stacks in the periphery. Each of the plurality of core gate stacks includes a first polysilicon gate and a WSi layer above the first polysilicon gate. The plurality of sources resides between a portion of the plurality of core gate stacks. Each of the plurality of periphery gate stacks includes a second polysilicon gate and a CoSi layer on the second polysilicon gate.